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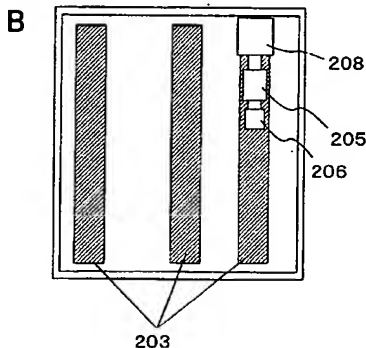
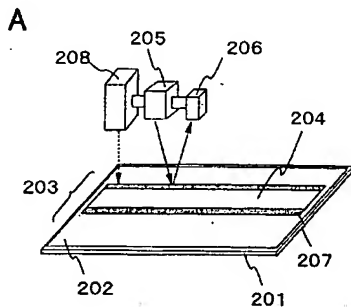
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(54) Title: LIGHT EXPOSURE APPARATUS AND MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE USING
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(57) Abstract: When annealing of a semiconductor film is conducted using a plurality of lasers, each of the distances between laser irradiation regions is different. When a lithography step is conducted in accordance with a marker which is formed over a substrate in advance after the step, light-exposure is not correctly conducted to a portion crystallized by laser. By using a laser irradiation region obtained on a laser irradiation step as a marker, light-exposure is conducted by making a light-exposure position of a stepper coincide with a large grain size region in the laser irradiation region. A large grain size region and a poorly crystalline region are detected by utilizing a thing that scattering intensity of light is different between the large grain size region and the poorly crystalline region, thereby determining a light-exposure position.

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